# Johann P Reithmaier

List of Publications by Year
in descending order

| # | Article | IF | Citations |
|---|---|---|---|
| 1 | Strong coupling in a single quantum dotâ€“semiconductor microcavity system. Nature, 2004, 432, 197-200. | 13.7 | 1,776 |
| 2 | Fine structure of neutral and charged excitons in self-assembled In(Ga)As/(Al)GaAs quantum dots. Physical Review B, 2002, 65, . | 1.1 | 933 |
| 3 | Introduction to the Special Issue on Semiconductor Lasers. IEEE Journal of Selected Topics in Quantum Electronics, 2017, 23, 1-3. | 1.9 | 539 |
| 4 | Electron and HolegFactors and Exchange Interaction from Studies of the Exciton Fine Structure inIn0.60Ga0.40AsQuantum Dots. Physical Review Letters, 1999, 82, 1748-1751. | 2.9 | 378 |
| 5 | Optical Modes in Photonic Molecules. Physical Review Letters, 1998, 81, 2582-2585. | 2.9 | 359 |
| 6 | Long-wavelength InP-based quantum-dash lasers. IEEE Photonics Technology Letters, 2002, 14, 735-737. | 1.3 | 166 |
| 7 | Control of Vertically CoupledInGaAs/GaAsQuantum Dots with Electric Fields. Physical Review Letters, 2005, 94, 157401. | 2.9 | 138 |
| 8 | InP based lasers and optical amplifiers with wire-/dot-like active regions. Journal Physics D: Applied Physics, 2005, 38, 2088-2102. | 1.3 | 134 |
| 9 | Size Dependence of Confined Optical Modes in Photonic Quantum Dots. Physical Review Letters, 1997, 78, 378-381. | 2.9 | 128 |
| 10 | Tunable photonic crystals fabricated in III-V semiconductor slab waveguides using infiltrated liquid crystals. Applied Physics Letters, 2003, 82, 2767-2769. | 1.5 | 128 |
| 11 | Zeeman splitting of excitons and biexcitons in singleIn0.60Ga0.40As/GaAsself-assembled quantum dots. Physical Review B, 1998, 58, R7508-R7511. | 1.1 | 121 |
| 12 | Weak and strong coupling of photons and excitons in photonic dots. Physical Review B, 1998, 57, 9950-9956. | 1.1 | 112 |
| 13 | Telecom-wavelength (1.5â€‰<i>Î¼</i>m) single-photon emission from InP-based quantum dots. Applied Physics Letters, 2013, 103, . | 1.5 | 111 |
| 14 | Transient electromagnetically induced transparency in self-assembled quantum dots. Applied Physics Letters, 2008, 92, . | 1.5 | 93 |
| 15 | Highly efficient GaInAs/(Al)GaAs quantum-dot lasers based on a single active layer versus 980 nm high-power quantum-well lasers. Applied Physics Letters, 2000, 77, 1419-1421. | 1.5 | 92 |
| 16 | Lasing in high-Q quantum-dot micropillar cavities. Applied Physics Letters, 2006, 89, 051107. | 1.5 | 92 |
| 17 | Optical Demonstration of a Crystal Band Structure Formation. Physical Review Letters, 1999, 83, 5374-5377. | 2.9 | 91 |
| 18 | Band offset in elastically strained InGaAs/GaAs multiple quantum wells determined by optical absorption and electronic Raman scattering. Applied Physics Letters, 1990, 56, 536-538. | 1.5 | 89 |

| # | Article | IF | Citations |
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| 19 | On the nature of quantum dash structures. Journal of Applied Physics, 2004, 95, 6103-6111. | 1.1 | 87 |
| 20 | High-performance GaInAs/GaAs quantum-dot lasers based on a single active layer. Applied Physics Letters, 1999, 74, 2915-2917. | 1.5 | 86 |
| 21 | Correlation between the gain profile and the temperature-induced shift in wavelength of quantum-dot lasers. Applied Physics Letters, 2002, 81, 217-219. | 1.5 | 86 |
| 22 | Size control of InAs quantum dashes. Applied Physics Letters, 2005, 86, 253112. | 1.5 | 84 |
| 23 | Er doped nanocrystalline ZnO planar waveguide structures for 1.55 Î¼m amplifier applications. Applied Physics Letters, 1999, 75, 2005-2007. | 1.5 | 83 |
| 24 | Low-threshold high-quantum-efficiency laterally gain-coupled InGaAs/AlGaAs distributed feedback lasers. Applied Physics Letters, 1999, 74, 483-485. | 1.5 | 82 |
| 25 | Line narrowing in single semiconductor quantum dots: Toward the control of environment effects. Physical Review B, 2002, 66, . | 1.1 | 78 |
| 26 | Semiconductor quantum dot microcavity pillars with high-quality factors and enlarged dot dimensions. Applied Physics Letters, 2005, 86, 111105. | 1.5 | 78 |
| 27 | Broad-band wavelength conversion based on cross-gain modulation and four-wave mixing in InAs-InP quantum-dash semiconductor optical amplifiers operating at 1550 nm. IEEE Photonics Technology Letters, 2003, 15, 563-565. | 1.3 | 77 |
| 28 | InAs/InP Quantum-Dash Lasers and Amplifiers. Proceedings of the IEEE, 2007, 95, 1779-1790. | 16.4 | 76 |
| 29 | Epitaxial growth of 1.55Î¼m emitting InAs quantum dashes on InP-based heterostructures by GS-MBE for long-wavelength laser applications. Journal of Crystal Growth, 2003, 251, 248-252. | 0.7 | 64 |
| 30 | High-temperature operating 1.3-Î¼m quantum-dot lasers for telecommunication applications. IEEE Photonics Technology Letters, 2001, 13, 764-766. | 1.3 | 59 |
| 31 | Strong excitonâ€“photon coupling in semiconductor quantum dot systems. Semiconductor Science and Technology, 2008, 23, 123001. | 1.0 | 59 |
| 32 | Optical properties ofGa0.8In0.2As/GaAs surface quantum wells. Physical Review B, 1993, 48, 14741-14744. | 1.1 | 58 |
| 33 | High gain 1.55â€‚Î¼m diode lasers based on InAs quantum dot like active regions. Applied Physics Letters, 2011, 98, . | 1.5 | 58 |
| 34 | The role of auger recombination in inas 1.3-Î¼m quantum-dot lasers investigated using high hydrostatic pressure. IEEE Journal of Selected Topics in Quantum Electronics, 2003, 9, 1300-1307. | 1.9 | 57 |
| 35 | Lateral coupling â€“ a material independent way to complex coupled DFB lasers. Optical Materials, 2001, 17, 19-25. | 1.7 | 52 |
| 36 | Investigation of the critical layer thickness in elastically strained InGaAs/GaAlAs quantum wells by photoluminescence and transmission electron microscopy. Applied Physics Letters, 1989, 54, 48-50. | 1.5 | 51 |

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| 37 | Polariton-polariton scattering in semiconductor microcavities: Experimental observation of thresholdlike density dependence. Physical Review B, 2000, 61, R2409-R2412. | 1.1 | 51 |
| 38 | Influence of the strain on the formation of GaInAs/GaAs quantum structures. Journal of Crystal Growth, 2006, 286, 6-10. | 0.7 | 49 |
| 39 | Edge-emitting GaInAs-AlGaAs microlasers. IEEE Photonics Technology Letters, 1999, 11, 943-945. | 1.3 | 48 |
| 40 | Influence of the As2/As4 growth modes on the formation of quantum dot-like InAs islands grown on InAlGaAs/InP (100). Applied Physics Letters, 2010, 96, 191903. | 1.5 | 48 |
| 41 | Enhancement of spontaneous emission rates by three-dimensional photon confinement in Bragg microcavities. Physical Review B, 1997, 56, R4367-R4370. | 1.1 | 47 |
| 42 | Influence of doping density on electron dynamics in GaAsâˆ•AlGaAs quantum cascade lasers. Journal of Applied Physics, 2006, 99, 103106. | 1.1 | 47 |
| 43 | Temperature stability of static and dynamic properties of 155 Âµm quantum dot lasers. Optics Express, 2018, 26, 6056. | 1.7 | 47 |
| 44 | Cell adhesion and growth on ultrananocrystalline diamond and diamond-like carbon films after different surface modifications. Applied Surface Science, 2014, 297, 95-102. | 3.1 | 46 |
| 45 | Bioproperties of nanocrystalline diamond/amorphous carbon composite films. Diamond and Related Materials, 2007, 16, 735-739. | 1.8 | 45 |
| 46 | Coherent photonic coupling of semiconductor quantum dots. Optics Letters, 2006, 31, 1738. | 1.7 | 43 |
| 47 | Single photon emission at 1.55â€‰Î¼m from charged and neutral exciton confined in a single quantum dash. Applied Physics Letters, 2014, 105, 021909. | 1.5 | 43 |
| 48 | Indium desorption during MBE growth of strained InGaAs layers. Journal of Crystal Growth, 1991, 111, 407-412. | 0.7 | 42 |
| 49 | High-temperature properties of GaInAs/AlGaAs lasers with improved carrier confinement by short-period superlattice quantum well barriers. Applied Physics Letters, 1998, 73, 2863-2865. | 1.5 | 41 |
| 50 | Ultrafast gain and index dynamics of quantum dash structures emitting at 1.55Î¼m. Applied Physics Letters, 2006, 89, 081102. | 1.5 | 41 |
| 51 | Large linewidth reduction in semiconductor lasers based on atom-like gain material. Optica, 2019, 6, 1071. | 4.8 | 41 |
| 52 | Experimental evidence for the transition from two- to three-dimensional behavior of excitons in quantum-well structures. Physical Review B, 1991, 43, 4933-4938. | 1.1 | 40 |
| 53 | High-performance 980 nm quantum dot lasers for high-power applications. Electronics Letters, 2001, 37, 353. | 0.5 | 40 |
| 54 | Multiple wavelength amplification in wide band high power 1550â€…nm quantum dash optical amplifier. Electronics Letters, 2004, 40, 760. | 0.5 | 40 |

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| 55 | Photoreflectance-probed excited states in InAsâˆ•InGaAlAs quantum dashes grown on InP substrate. Applied Physics Letters, 2006, 89, 031908. | 1.5 | 40 |
| 56 | Telecom wavelength single quantum dots with very small excitonic fine-structure splitting. Applied Physics Letters, 2018, 112, . | 1.5 | 40 |
| 57 | Gain and noise saturation of wide-band InAs-InP quantum dash optical amplifiers: model and experiments. IEEE Journal of Selected Topics in Quantum Electronics, 2005, 11, 1015-1026. | 1.9 | 38 |
| 58 | Tribological properties of ultrananocrystalline diamond films in various test atmosphere. Tribology International, 2011, 44, 2042-2049. | 3.0 | 38 |
| 59 | High-density 1.54 Î¼m InAs/InGaAlAs/InP(100) based quantum dots with reduced size inhomogeneity. Journal of Crystal Growth, 2015, 425, 299-302. | 0.7 | 38 |
| 60 | Single-photon emission of InAs/InP quantum dashes at 1.55â€‰<i>Î¼</i>m and temperatures up to 80â€‰K. Applied Physics Letters, 2016, 108, . | 1.5 | 38 |
| 61 | Strong variation of the excitongfactors in self-assembledIn0.60Ga0.40Asquantum dots. Physical Review B, 1999, 60, R8481-R8484. | 1.1 | 37 |
| 62 | InAsâˆ•InP 1550â€…nm quantum dash semiconductor optical amplifiers. Electronics Letters, 2002, 38, 1350. | 0.5 | 37 |
| 63 | Radiative emission dynamics of quantum dots in a single cavity micropillar. Physical Review B, 2006, 74, . | 1.1 | 37 |
| 64 | Focused ion-beam implantation induced thermal quantum-well intermixing for monolithic optoelectronic device integration. IEEE Journal of Selected Topics in Quantum Electronics, 1998, 4, 595-605. | 1.9 | 36 |
| 65 | Optical gain properties of InAsâˆ•InAlGaAsâˆ•InP quantum dash structures with a spectral gain bandwidth of more than 300nm. Applied Physics Letters, 2006, 89, 061107. | 1.5 | 36 |
| 66 | Highâ€Purity Triggered Singleâ€Photon Emission from Symmetric Single InAs/InP Quantum Dots around the Telecom Câ€Band Window. Advanced Quantum Technologies, 2020, 3, 1900082. | 1.8 | 35 |
| 67 | Optical spectroscopy of single InAs/InGaAs quantum dots in a quantum well. Applied Physics Letters, 2002, 81, 4898-4900. | 1.5 | 34 |
| 68 | Exciton-photon coupling in photonic wires. Physical Review B, 1998, 57, R6807-R6810. | 1.1 | 33 |
| 69 | Rabi oscillations and self-induced transparency in InAs/InP quantum dot semiconductor optical amplifier operating at room temperature. Optics Express, 2013, 21, 26786. | 1.7 | 33 |
| 70 | Exciton and biexciton dynamics in single self-assembled InAs/InGaAlAs/InP quantum dash emitting near 1.55â€‰<i>Î¼</i>m. Applied Physics Letters, 2013, 103, . | 1.5 | 33 |
| 71 | High Speed 1.55 Î¼m InAs/InGaAlAs/InP Quantum Dot Lasers. IEEE Photonics Technology Letters, 2014, 26, 11-13. | 1.3 | 33 |
| 72 | Magneto-optical investigations of single self-assembled InAs/InGaAlAs quantum dashes. Applied Physics Letters, 2003, 82, 2799-2801. | 1.5 | 32 |

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| 73 | Cross-gain modulation in inhomogeneously broadened gain spectra of InP-Based 1550 nm quantum dash optical amplifiers: Small-signal bandwidth dependence on wavelength detuning. Applied Physics Letters, 2003, 82, 4660-4662. | 1.5 | 32 |
| 74 | Temperature-Insensitive High-Speed Directly Modulated 1.55-<inline-formula> <tex-math notation="LaTeX">$mu ext{m}$ </tex-math> </inline-formula> Quantum Dot Lasers. IEEE Photonics Technology Letters, 2016, 28, 2451-2454. | 1.3 | 32 |
| 75 | Laser emission from photonic dots. Applied Physics Letters, 1997, 71, 488-490. | 1.5 | 31 |
| 76 | Enhanced direct-modulated bandwidth of 37â€…GHz by a multi-section laser with a coupled-cavity-injection-grating design. Electronics Letters, 2003, 39, 1592. | 0.5 | 31 |
| 77 | High frequency characteristics of InAs/GaInAs quantum dot distributed feedback lasers emitting at 1.3 [micro sign]m. Electronics Letters, 2001, 37, 1223. | 0.5 | 30 |
| 78 | Photoreflectance spectroscopy of vertically coupled InGaAs/GaAs double quantum dots. Solid State Communications, 2001, 117, 401-406. | 0.9 | 30 |
| 79 | High-power quantum dot lasers with improved temperature stability of emission wavelength for uncooled pump sources. Electronics Letters, 2005, 41, 1125. | 0.5 | 30 |
| 80 | High-Speed Low-Noise InAs/InAlGaAs/InP 1.55-$mu{m m}$ Quantum-Dot Lasers. IEEE Photonics Technology Letters, 2012, 24, 809-811. | 1.3 | 30 |
| 81 | Optically probed wetting layer in InAs/InGaAlAs/InP quantum-dash structures. Applied Physics Letters, 2005, 86, 101904. | 1.5 | 29 |
| 82 | Wettability and protein adsorption on ultrananocrystalline diamond/amorphous carbon composite films. Diamond and Related Materials, 2009, 18, 895-898. | 1.8 | 29 |
| 83 | Heterodyne pump probe measurements of nonlinear dynamics in an indium phosphide photonic crystal cavity. Applied Physics Letters, 2013, 103, . | 1.5 | 29 |
| 84 | High-power 980â€…nm quantum dot broad area lasers. Electronics Letters, 2003, 39, 1655. | 0.5 | 28 |
| 85 | Electronic structure, morphology and emission polarization of enhanced symmetry InAs quantum-dot-like structures grown on InP substrates by molecular beam epitaxy. Journal of Applied Physics, 2013, 114, . | 1.1 | 28 |
| 86 | Exciton lifetime and emission polarization dispersion in strongly in-plane asymmetric nanostructures. Physical Review B, 2017, 96, . | 1.1 | 28 |
| 87 | Dynamics of carrier-capture processes inGaxIn1â^'xAs/GaAs near-surface quantum wells. Physical Review B, 1995, 51, 4657-4660. | 1.1 | 27 |
| 88 | Improved performance of MBE grown quantum-dot lasers with asymmetric dots in a well design emitting near 1.3Î¼m. Journal of Crystal Growth, 2003, 251, 742-747. | 0.7 | 27 |
| 89 | High-gain wavelength-stabilized 1.55 <i>Î¼</i>m InAs/InP(100) based lasers with reduced number of quantum dot active layers. Applied Physics Letters, 2013, 102, . | 1.5 | 27 |
| 90 | Large anisotropy of electron and hole<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mi>g</mml:mi></mml:math>factors in infrared-emitting InAs/InAlGaAs self-assembled quantum dots. Physical Review B, 2016, 93, . | 1.1 | 27 |

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| 91 | Minimum feature sizes and ion beam profile for a focused ion beam system with post-objective lens retarding and acceleration mode. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1994, 12, 3518. | 1.6 | 26 |
| 92 | Telecom wavelength emitting single quantum dots coupled to InP-based photonic crystal microcavities. Applied Physics Letters, 2017, 110, . | 1.5 | 26 |
| 93 | Widely tunable narrow-linewidth 1.5 <i>Î¼</i>m light source based on a monolithically integrated quantum dot laser array. Applied Physics Letters, 2017, 110, . | 1.5 | 26 |
| 94 | InAs/GaInAs quantum dot DFB lasers emitting at 1.3 [micro sign]m. Electronics Letters, 2001, 37, 634. | 0.5 | 25 |
| 95 | Wide range tunable laterally coupled distributed-feedback lasers based on InGaAs-GaAs quantum dots. IEEE Photonics Technology Letters, 2002, 14, 1246-1248. | 1.3 | 25 |
| 96 | High-Power Tunnel-Injection 1060-nm InGaAsâ€“(Al)GaAs Quantum-Dot Lasers. IEEE Photonics Technology Letters, 2009, 21, 999-1001. | 1.3 | 25 |
| 97 | Influence of electronic coupling on the radiative lifetime in the (In,Ga)As/GaAs quantum dotâ€“quantum well system. Physical Review B, 2012, 85, . | 1.1 | 25 |
| 98 | Rabi oscillations in a room-temperature quantum dash semiconductor optical amplifier. Physical Review B, 2014, 90, . | 1.1 | 25 |
| 99 | Importance of Auger recombination in InAs 1.3â€…[micro sign]m quantum dot lasers. Electronics Letters, 2003, 39, 58. | 0.5 | 24 |
| 100 | Gain, index variation, and linewidth-enhancement factor in 980-nm quantum-well and quantum-dot lasers. IEEE Journal of Quantum Electronics, 2005, 41, 117-126. | 1.0 | 24 |
| 101 | Plasma amination of ultrananocrystalline diamond/amorphous carbon composite films for the attachment of biomolecules. Diamond and Related Materials, 2011, 20, 254-258. | 1.8 | 24 |
| 102 | Low temperature growth of nanocrystalline and ultrananocrystalline diamond films: A comparison. Physica Status Solidi (A) Applications and Materials Science, 2012, 209, 1664-1674. | 0.8 | 24 |
| 103 | All-optical signal processing at 10â€‰GHz using a photonic crystal molecule. Applied Physics Letters, 2013, 103, . | 1.5 | 24 |
| 104 | Confinement of light hole valenceâ€band states in pseudomorphic InGaAs/Ga(Al)As quantum wells. Applied Physics Letters, 1990, 57, 957-959. | 1.5 | 23 |
| 105 | 22-GHz Modulation Bandwidth of Long Cavity DBR Laser by Using a Weakly Laterally Coupled Grating Fabricated by Focused Ion Beam Lithography. IEEE Photonics Technology Letters, 2004, 16, 18-20. | 1.3 | 23 |
| 106 | Reduction of the threshold current density of GaAs/AlGaAs quantum cascade lasers by optimized injector doping and growth conditions. Journal of Crystal Growth, 2005, 278, 775-779. | 0.7 | 23 |
| 107 | Polarization-dependent optical properties of planar photonic crystals infiltrated with liquid crystals. Applied Physics Letters, 2005, 87, 121105. | 1.5 | 23 |
| 108 | Thermal quenching of photoluminescence from InAsâˆ•In0.53Ga0.23Al0.24Asâˆ•InP quantum dashes with different sizes. Applied Physics Letters, 2006, 89, 151902. | 1.5 | 23 |

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| 109 | Optical properties of low-strained InxGa1âˆ’xAsâˆ•GaAs quantum dot structures at the two-dimensionalâ€“three-dimensional growth transition. Journal of Applied Physics, 2006, 100, 013503. | 1.1 | 23 |
| 110 | A nearly instantaneous gain response in quantum dash based optical amplifiers. Applied Physics Letters, 2010, 97, . | 1.5 | 23 |
| 111 | Low-density InP-based quantum dots emitting around the 1.5â€‰<i>Î¼</i>m telecom wavelength range. Applied Physics Letters, 2014, 104, . | 1.5 | 23 |
| 112 | Electron and hole<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mi>g</mml:mi></mml:math>factors in InAs/InAlGaAs self-assembled quantum dots emitting at telecom wavelengths. Physical Review B, 2015, 92, . | 1.1 | 23 |
| 113 | Short-cavity edge-emitting lasers with deeply etched distributed Bragg mirrors. Electronics Letters, 1999, 35, 154. | 0.5 | 22 |
| 114 | Single-mode distributed feedback and microlasers based on quantum-dot gain material. IEEE Journal of Selected Topics in Quantum Electronics, 2002, 8, 1035-1044. | 1.9 | 22 |
| 115 | Deeply etched two-dimensional photonic crystals fabricated on GaAs/AlGaAs slab waveguides by using chemically assisted ion beam etching. Microelectronic Engineering, 2002, 61-62, 875-880. | 1.1 | 22 |
| 116 | Static and dynamic properties of laterally coupled DFB lasers based on InAsâˆ•InP QDash structures. Electronics Letters, 2005, 41, 808. | 0.5 | 22 |
| 117 | Complex (As2S3)(100âˆ’)(AgI) chalcogenide glasses for gas sensors. Sensors and Actuators B: Chemical, 2009, 143, 395-399. | 4.0 | 22 |
| 118 | Phonon-assisted radiative recombination of excitons confined in strongly anisotropic nanostructures. Physical Review B, 2014, 90, . | 1.1 | 22 |
| 119 | Incorporation and study of SiV centers in diamond nanopillars. Diamond and Related Materials, 2016, 64, 64-69. | 1.8 | 22 |
| 120 | Patterning of the surface termination of ultrananocrystalline diamond films for guided cell attachment and growth. Surface and Coatings Technology, 2017, 321, 229-235. | 2.2 | 22 |
| 121 | Gallium desorption during growth of (Al,Ga)As by molecular beam epitaxy. Applied Physics Letters, 1992, 61, 1222-1224. | 1.5 | 21 |
| 122 | Photonic defect states in chains of coupled microresonators. Physical Review B, 2001, 64, . | 1.1 | 21 |
| 123 | Recent advances in semiconductor quantum-dot lasers. Comptes Rendus Physique, 2003, 4, 611-619. | 0.3 | 21 |
| 124 | Recombination mechanisms in InAs/InP quantum dash lasers studied using high hydrostatic pressure. Physica Status Solidi (B): Basic Research, 2004, 241, 3427-3431. | 0.7 | 21 |
| 125 | Photoreflectance determination of the wetting layer thickness in the InxGa1âˆ’xAsâˆ•GaAs quantum dot system for a broad indium content range of 0.3â€“1. Journal of Applied Physics, 2006, 100, 103529. | 1.1 | 21 |
| 126 | Magnetic field control of the neutral and charged exciton fine structure in single quantum dashes emitting at 1.55â€‰Î¼m. Applied Physics Letters, 2015, 106, 053114. | 1.5 | 21 |

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| 127 | InP-based single-photon sources operating at telecom C-band with increased extraction efficiency. Applied Physics Letters, 2021, 118, . | 1.5 | 21 |
| 128 | First order gainâ€coupled GaInAs/GaAs distributed feedback laser diodes patterned by focused ion beam implantation. Applied Physics Letters, 1996, 69, 1906-1908. | 1.5 | 20 |
| 129 | High-frequency properties of 1.55 Î¼m laterally complex coupled distributed feedback lasers fabricated by focused-ion-beam lithography. Applied Physics Letters, 2000, 77, 325-327. | 1.5 | 20 |
| 130 | High Performance 1.3 Âµm Quantum-Dot Lasers. Japanese Journal of Applied Physics, 2002, 41, 1158-1161. | 0.8 | 20 |
| 131 | InP-based quantum dash lasers for wide gain bandwidth applications. Journal of Crystal Growth, 2005, 278, 346-350. | 0.7 | 20 |
| 132 | On the development of the morphology of ultrananocrystalline diamond films. Physica Status Solidi (A) Applications and Materials Science, 2011, 208, 70-80. | 0.8 | 20 |
| 133 | Coherent control in a semiconductor optical amplifier operating at room temperature. Nature Communications, 2014, 5, 5025. | 5.8 | 20 |
| 134 | Deterministic Arrays of Epitaxially Grown Diamond Nanopyramid<i>s</i> with Embedded Siliconâ€Vacancy Centers. Advanced Optical Materials, 2019, 7, 1800715. | 3.6 | 20 |
| 135 | InGaAs/AlGaAs quantum dot DFB lasers operating up to 213Â°C. Electronics Letters, 1999, 35, 2036. | 0.5 | 20 |
| 136 | Highly Resolved Maskless Patterning on InP by Focused Ion Beam Enhanced Wet Chemical Etching. Japanese Journal of Applied Physics, 1999, 38, 6142-6144. | 0.8 | 19 |
| 137 | 1.55 Î¼m single mode lasers with complex coupled distributed feedback gratings fabricated by focused ion beam implantation. Applied Physics Letters, 1999, 75, 1491-1493. | 1.5 | 19 |
| 138 | Near-field mapping of the electromagnetic field in confined photon geometries. Physical Review B, 2002, 66, . | 1.1 | 19 |
| 139 | High brightness GaInAs/(Al)GaAs quantum-dot tapered lasers at 980 nm with high wavelength stability. Applied Physics Letters, 2004, 84, 2238-2240. | 1.5 | 19 |
| 140 | Time-resolved chirp in an InAsâˆ•InP quantum-dash optical amplifier operating with 10Gbitâˆ•s data. Applied Physics Letters, 2005, 87, 021104. | 1.5 | 19 |
| 141 | GaInAs/(Al)GaAs quantum-dot lasers with high wavelength stability. Semiconductor Science and Technology, 2008, 23, 085022. | 1.0 | 19 |
| 142 | Tribological properties of nanocrystalline diamond films deposited by hot filament chemical vapor deposition. AIP Advances, 2012, 2, . | 0.6 | 19 |
| 143 | 50 mW CW-operated single-mode surface-emitting AlGaAs lasers with 45 degrees total reflection mirrors. IEEE Photonics Technology Letters, 1992, 4, 698-700. | 1.3 | 18 |
| 144 | Nanocrystalline diamond/amorphous carbon composite coatings for biomedical applications. Diamond and Related Materials, 2008, 17, 882-887. | 1.8 | 18 |

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| 145 | Investigation of the UV/O<sub>3</sub> treatment of ultrananocrystalline diamond films. Surface and Interface Analysis, 2010, 42, 1152-1155. | 0.8 | 18 |
| 146 | Electrical properties of ultrananocrystalline diamond/amorphous carbon nanocomposite films. Diamond and Related Materials, 2010, 19, 449-452. | 1.8 | 18 |
| 147 | Excitonic fine structure and binding energies of excitonic complexes in single InAs quantum dashes. Physical Review B, 2016, 94, . | 1.1 | 18 |
| 148 | 12 [micro sign]m long edge-emitting quantum-dot laser. Electronics Letters, 2001, 37, 690. | 0.5 | 17 |
| 149 | On the tunnel injection of excitons and free carriers from In0.53Ga0.47Asâˆ•In0.53Ga0.23Al0.24As quantum well to InAsâˆ•In0.53Ga0.23Al0.24As quantum dashes. Applied Physics Letters, 2006, 89, 061902. | 1.5 | 17 |
| 150 | Widely tunable single-mode quantum cascade lasers with two monolithically coupled Fabry-PÃ©rot cavities. Applied Physics Letters, 2006, 89, 241126. | 1.5 | 17 |
| 151 | Cross talk free multi channel processing of 10 Gbit/s data via four wave mixing in a 1550 nm InAs/InP quantum dash amplifier. Optics Express, 2008, 16, 19072. | 1.7 | 17 |
| 152 | Nanocrystalline diamond containing hydrogels and coatings for acceleration of osteogenesis. Diamond and Related Materials, 2011, 20, 165-169. | 1.8 | 17 |
| 153 | Height-driven linear polarization of the surface emission from quantum dashes. Semiconductor Science and Technology, 2012, 27, 105022. | 1.0 | 17 |
| 154 | Highâ€power singleâ€mode AlGaAs lasers with bentâ€waveguide nonabsorbing etched mirrors. Journal of Applied Physics, 1992, 72, 2131-2135. | 1.1 | 16 |
| 155 | Transform-limited picosecond optical pulses from a mode-locked InGaAs/AlGaAs QW laser with integrated passive waveguide cavity and QW modulator. IEEE Photonics Technology Letters, 1993, 5, 896-899. | 1.3 | 16 |
| 156 | First order gain and index coupled distributed feedback lasers in ZnSeâ€based structures with finely tunable emission wavelengths. Applied Physics Letters, 1996, 68, 599-601. | 1.5 | 16 |
| 157 | Enhanced exciton-phonon scattering inInxGa1âˆ’xAs/GaAsquantum wires. Physical Review B, 1997, 56, 12096-12099. | 1.1 | 16 |
| 158 | GaAsâˆ•AlGaAs quantum cascade micro lasers based on monolithic semiconductor-air Bragg mirrors. Electronics Letters, 2004, 40, 120. | 0.5 | 16 |
| 159 | Spectrally resolved dynamics of inhomogeneously broadened gain in InAsâˆ•InP1550nm quantum-dash lasers. Applied Physics Letters, 2004, 85, 5505-5507. | 1.5 | 16 |
| 160 | Device performance and wavelength tuning behavior of ultra-short quantum-cascade microlasers with deeply etched Bragg-mirrors. IEEE Journal of Selected Topics in Quantum Electronics, 2005, 11, 1048-1054. | 1.9 | 16 |
| 161 | Modulation speed enhancement by coupling to higher order resonances: a road towards 40 GHz bandwidth lasers on InP. , 0, , . | | 16 |
| 162 | Dependence of saturation effects on electron confinement and injector doping in GaAsâˆ•Al0.45Ga0.55As quantum-cascade lasers. Applied Physics Letters, 2006, 88, 251109. | 1.5 | 16 |

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| 163 | Microthermography of diode lasers: The impact of light propagation on image formation. Journal of Applied Physics, 2009, 105, 014502. | 1.1 | 16 |
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